

Structural, electronic, and magnetic properties of ilmenite FeTiO₃

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Abstract:

The electronic structure and magnetic properties of ilmenite FeTiO₃ were studied by first principle calculations [1]. Ilmenite is a wide-band-gap semiconductor with a 2.5 eV band gap [2], which is exploited to realize multifunctional devices [3]. The ilmenite structure is based on a hexagonal-close-packed oxygen lattice with metal atoms Fe and Ti occupying two-thirds of the available octahedral sites. Each octahedron shares three edges with octahedra inside the layer, a face with an octahedron of the second type of cation in the adjacent layer, and the opposite face with a vacant octahedral site. In other words, layers of Fe and Ti alternate with a cation ordering of Ti-Fe-V-Fe-Ti, V: vacant sites along the c axis.

We present calculations related to the structural properties: total energies, lattice constants, and bulk moduli. We also report the total and local magnetic moments and the spin-polarized densities of states. We considered both the ferromagnetic state and an antiferromagnetic configuration found stable in ilmenite in which the Fe²⁺ spins are ferromagnetically aligned within a bilayer but antiferromagnetically coupled between bilayers: no differences in magnetic moment and electron charge of iron were found between the magnetic configurations.

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